

UMW SI2303

-30V P-Channel MOSFET

1.Features

- V_{DS(V)}=-30V
- I_D=-1.7A

2.Application

Load Switch for Portable Devices

- R_{DS(ON)}<190mΩ(V_{GS}=-10V)
- R_{DS(ON)}<330mΩ(V_{GS}=-4.5V)
- DC/DC Converter

3. Pinning information

Pin	Symbol	Description	SOT-23 3	_Գ D
1	G	GATE		
2	S	SOURCE		
3	D	DRAIN	1	G S

4.Absolute Maximum Ratings T_A= 25°C

Parameter	Symbol	Rating	Units	
Drain-Source Voltage	V _{DS}	-30	V	
Gate-Source Voltage	V _{GS}	±20 V		
Continuous Drain Curren	۱ _D	-1.7		
Pulsed Drain Current	I _{DM}	-10	A	
Continuous Source-Drain Current(Diode Conduction)	I _S	-1		
Power Dissipation	P _D	0.9	W	
Thermal Resistance from Junction to Ambient (t≤5s)	R _{eja}	357	°C/W	
Operating Junction	TJ	150	°C	
Storage Temperature	T _{stg}	-55 to 150	°C	



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5. Electrical Characteristics $T_A = 25^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Static			•		•	
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250µA	-30			V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250µA	-1		-3	V
Gate-source leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
	D	V _{GS} =-10V, I _D =-1.7A		120	190	mΩ
Drain-source on-state resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-1.3A		150	330	mΩ
Forward transconductance	g _{FS}	V _{DS} =-10V, I _D =-1.7A	5.5			s
Diode forward voltage	V _{SD}	I _S =-1A, V _{GS} =0V		-0.8	-1.2	V
Dynamic			•		•	
Input Capacitance	C _{iss}			155		pF
Output Capacitance	C _{oss}	V _{DS} =-15V, V _{GS} =0V, f=1MHz		35		pF
Reverse Transfer Capacitance	C _{rss}			25		pF
Total gate charge	charge Q _g			2	4	nC
Gate-source charge	Q _{gs}	V _{DS} =-15V, V _{GS} =-4.5V		0.6		nC
Gate-drain charge	Q _{gd}	I _D =-1.7A		1		nC
Gate resistance	R _g	f=1MHz		8.5	17	Ω
Switchingb			•		•	
Turn-On Delay Time	t _{D(on)}	$\gamma = 45\gamma$		36	44	ns
Rise Time	t _r	V_{DD} =-15V		37	45	ns
Turn-Off Delay Time	t _{D(off)}	R _L =10Ω, I _D ≈-1.5A		12	18	ns
Fall time	t _f	V _{GEN} =-4.5V, R _G =5Ω		9	14	ns
Drain-Source Body Diode Characteristics					•	
Continuous Source-Drain Diode Current	Is	T _c =25°C			-1.75	Α
Pulsed Diode forward Current	I _{SM}				-10	Α
				-		

1. Repetitive rating : Pulse width limited by junction temperature.

3. Pulse Test : Pulse Width≤300µs, Duty Cycle≤2%.

2. Surface mounted on FR4 board , t < 5 sec.

4. Guaranteed by design, not subject to production testing.





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6.SOT-23 Package Outline Dimensions





DIMENSIONS (mm are the original dimensions)

Symbol	Α	В	bp	С	D	E	Η _E	A1	L _p
Min	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20
Мах	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50



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7.Ordering information



yww: Batch Code

Order Code	Order Code Package		Delivery Mode		
UMW SI2303	UMW SI2303 SOT-23		Tape and reel		





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8.Disclaimer

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